TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# T C 7 M H 2 7 3 F K

Octal D-Type Flip Flop with Clear

The TC7MH273FK is an advanced high speed CMOS octal D-type flip-flop fabricated with silicon gate  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

Information signals applied to D inputs are transferred to the Q outputs on the positive going edge of the clock pulse.

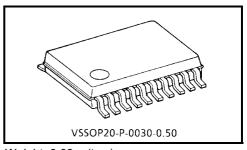
When the  $\overline{\text{CLR}}$  input is held "L", the Q outputs are at a low logic level independent of the other inputs.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This

device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

#### Features

- High speed:  $f_{max} = 165 \text{ MHz} (typ.) (V_{CC} = 5 \text{ V})$
- Low power dissipation:  $I_{CC} = 4 \mu A (max) (T_a = 25^{\circ}C)$
- High noise immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range:  $V_{CC}$  (opr) = 2~5.5 V
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with 74ALS273





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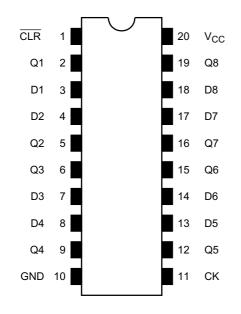
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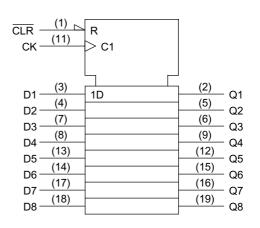
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## <u>TOSHIBA</u>

## Pin Assignment (top view)



## **IEC Logic Symbol**

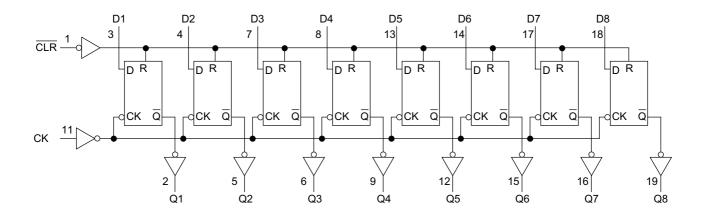


#### Truth Table

	Inputs		Function	
CLR	D	СК	Q	Tunction
L	Х	Х	L	Clear
Н	L		L	—
Н	Н		Н	—
н	Х		Qn	No change

X: Don't care

## System Diagram



## **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	IOUT	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	age V <sub>CC</sub>		V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 $\pm$ 0.3 V)	ns/V
	ut/uv	$0 \sim 20 \ (V_{CC} = 5 \pm 0.5 \ V)$	115/ V

## **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol	Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit	
Charac	Stenstics	Symbol			$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Onit	
					2.0	1.50	_		1.50	_		
Input voltage	"H" level	VIH	—		3.0~5.5	$V_{CC} \times 0.7$		—	$V_{CC} \times 0.7$	—	v	
input voltage					2.0		_	0.50	_	0.50	v	
	"L" level	VIL	—		3.0~5.5	—	—	$V_{CC} \times 0.3$	_	$V_{CC} \times 0.3$		
	"H" level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	2.0	1.9	2.0	_	1.9	_		
					3.0	2.9	3.0	—	2.9	—		
					4.5	4.4	4.5	—	4.4	—		
Output				$I_{OH} = -4 \text{ mA}$	3.0 2.58 — —		2.48	—				
				I <sub>OH</sub> = -8 mA	4.5	3.94	_	—	3.80	—	v	
voltage		evel V <sub>OL</sub>			2.0	_	0	0.1	_	0.1	v	
				$I_{OL} = 50 \ \mu A$	3.0	—	0	0.1	—	0.1		
	"L" level		$V_{IN} = V_{IH}$ or $V_{IL}$		4.5	_	0	0.1	—	0.1		
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44		
				$I_{OL} = 8 \text{ mA}$	4.5	—	—	0.36	—	0.44		
Input leakage	current	I <sub>IN</sub>	$I_{IN}$ $V_{IN} = 5.5$ V or GND		0~5.5		_	±0.1		±1.0	μA	
Quiescent supply current $I_{CC}$ $V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μA				

## Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Symbol Test Condition		Ta = 25°C		Ta = -40~85°C	Unit
	Symbol			Тур.	Limit	Limit	Onit
Minimum pulse width	t <sub>w (L)</sub>		$3.3\pm 0.3$	_	5.5	6.5	ns
(CK)	t <sub>w (H)</sub>		$5.0\pm0.5$	—	5.0	5.0	ns
Minimum pulse width	4		$3.3\pm 0.3$	—	5.0	6.0	ns
( CLR )	<sup>t</sup> w (L)		$5.0\pm0.5$	—	5.0	5.0	115
Minimum set-up time	t <sub>s</sub>	—	$3.3\pm 0.3$	—	5.5	6.5	ns
Minimum set-up time			$5.0\pm0.5$		4.5	4.5	115
Minimum hold time	+.		$3.3\pm 0.3$	—	1.0	1.0	ns
Minimum hold time t <sub>h</sub>		$5.0\pm0.5$	—	1.0	1.0	115	
Minimum removal time	+		$3.3\pm 0.3$	—	2.5	2.5	ns
( CLR )	rem	t <sub>rem</sub> — 5	$5.0\pm0.5$	_	2.0	2.0	115

#### AC Characteristics (Input: $t_r = t_f = 3 ns$ )

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		Unit
Symbo		Test Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Onit
			$3.3\pm0.3$	15	_	8.7	13.6	1.0	16.0	ns
Propagation delay time	t <sub>pLH</sub>			50	_	11.2	17.1	1.0	19.5	
(CK-Q)	t <sub>pHL</sub>		$5.0 \pm 0.5$	15	_	5.8	9.0	1.0	10.5	115
			5.0 ± 0.5	50	_	7.3	11.0	1.0	12.5	
			$3.3\pm0.3$	15	_	8.9	13.6	1.0	16.0	
Propagation delay time	t <sub>рНL</sub>	—	$3.3 \pm 0.3$	50		11.4	17.1	1.0	19.5	ns
( <u>CLR</u> -Q)			$5.0\pm0.5$	15		5.2	8.5	1.0	10.0	115
				50		6.7	10.5	1.0	12.0	
	f <sub>max</sub>	_	$3.3\pm0.3$	15	75	120		65	_	MHz
Maximum clock frequency				50	50	75		45	—	
Maximum clock frequency			$5.0\pm0.5$	15	120	165		100	_	
				50	80	110		70	_	
Output to output skew	t <sub>osLH</sub>	(Note1)	$3.3\pm 0.3$	50	_	—	1.5	_	1.5	ns
Oulput to oulput skew	t <sub>osHL</sub>		$5.0\pm0.5$	50		_	1.0		1.0	115
Input capacitance	C <sub>IN</sub>		_			4	10		10	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note2)		31		_		pF

Note1: This parameter is guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \ t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|$ 

Note2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

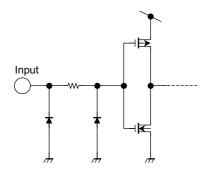
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$ 

And the total C<sub>PD</sub> when n pcs of flip-flop operate can be gained by the following equation: C<sub>PD</sub> (total) = 22 + 9  $\cdot$  n

Noise Characteristics (Input:  $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta = 25°C		- Unit
	Symbol	Test Condition	$V_{CC}\left(V\right)$	Тур.	Limit	Onit
Quiet output maximum dynamic $V_{OL}$	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	0.5	0.8	V
Quiet output minimum dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.5	-0.8	V
Minimum high level dynamic input voltage $V_{IH}$	VIHD	C <sub>L</sub> = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage $V_{IL}$	V <sub>ILD</sub>	$C_L = 50 \text{ pF}$	5.0		1.5	V

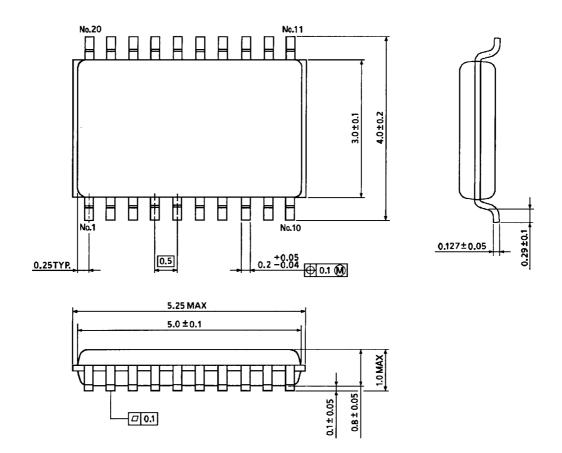
## Input Equivalent Circuit



## **Package Dimensions**

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)